L Number	Hits	Search Text	DB	Time stamp
1	6152	cathode same (etch\$2 or etching or electro\$1etch\$3 or electro\$1polish\$3)	USPAT	2003/11/25
2	3338	(cathode same (etch\$2 or etching or electro\$letch\$3 or electro\$lpolish\$3)) and semiconductor	USPAT	2003/11/25 10:35
3	2101	((cathode same (etch\$2 or etching or electro\$1etch\$3 or electro\$1polish\$3)) and semiconductor) and ((power or current	USPAT	2003/11/25 10:36
4	1706	or voltage) with cathode) (((cathode same (etch)2 or etching or electro\$letch\$3 or electro\$lpolish\$3)) and semiconductor) and ((power or current or voltage) with cathode)) and anode	USPAT	2003/11/25 10:38
5	1680	((((cathode same (etch\$2 or etching or electro\$1etch\$3 or electro\$1polish\$3)) and semiconductor) and ((power or current or voltage) with cathode)) and anode) and @av<=2001	USPAT	2003/11/25
6 .	594	(((((cathode same (etch\$2 or etching or electro\$1etch\$3 or electro\$1polish\$3)) and semiconductor) and ((power or current or voltage) with cathode)) and anode) and @ay<=2001) and (copper or Cu)	USPAT	2003/11/25
7	246	(((((cathode same (etch\$2 or etching or electro\$letch\$3 or electro\$lpolish\$3)) and semiconductor) and ((power or current or voltage) with cathode)) and anode) and @ay<=2001) and ((etch or etching or etched or electro\$letch\$3) same (copper or Cu)	USPAT	2003/11/25 10:46
8	206	((((((cathode same (etch\$2 or etching or electro\$1etch\$3 or electro\$1polish\$3)) and semiconductor) and ((power or current or voltage) with cathode)) and anode) and gay<=2001) and ((etch or etching or etched or electro\$1etch\$3) same (copper or Cu))) and (mask or plate or hard\$1mask)	USPAT	2003/11/25
9	12	("3959089"   "5256565"   "5567300"   "5863412"   "5993637"   "6017437"   "6056869"   "6077412"   "6171467"   "6176992"   "6299741"   "6328872").PN.	USPAT	2003/11/25
10	2	("4871416"   "5686789").PN.	USPAT	2003/11/25
11	153	<pre>(((((((cathode same (etch\$2 or etching or electro\$1etch\$3 or electro\$1polish\$3)) and semiconductor) and ((power or current or voltage) with cathode)) and anode) and @ay&lt;=2001) and ((etch or etching or etched or electro\$1etch\$3) same (copper or Cu))) and (mask or plate or hard\$1mask)) and @py&lt;=2001</pre>	USPAT	2003/11/25 11:33
12	58	<pre>(((((((cathode same (etch\$2 or etching or electro\$1etch\$3 or electro\$1polish\$3)) and semiconductor) and ((power or current or voltage) with cathode)) and anode) and @ay&lt;=2001) and ((etch or etching or etched or electro\$1etch\$3) same (copper or Cu))) and (mask or plate or hard\$1mask)) and @py&lt;=2001) not plasma</pre>	USPAT	2003/11/25

23	31	(((cathode near4 (plurality or second or two)) and semiconductor) and anode) and	USPAT	2003/11/25 13:57
	1	(electro\$letch or electro\$letching or	1	
24	15	electro\$1polish or electro\$1polishing)	USPAT	2003/11/25
44	15	<pre>((((cathode near4 (plurality or second or two)) and semiconductor) and anode) and (electro\$letch or electro\$letching or</pre>	OSPAI	13:55
		electro\$1polish or electro\$1polishing))		
	1	not (((electro\$letch or electro\$letching)	1	
		and semiconductor) and Gay<=2001)	1	
25	771	electro\$letch or electro\$letching or	US-PGPUB;	2003/11/25
	1	electro\$1polish or electro\$1polishing	EPO; JPO	13:58
26	548	(electro\$1etch or electro\$1etching or	US-PGPUB;	2003/11/25
		electro\$1polish or electro\$1polishing) and @ay<=2001	EPO; JPO	13:58
27	142	((electro\$letch or electro\$letching or	US-PGPUB;	2003/11/25
		electro\$1polish or electro\$1polishing)	EPO; JPO	14:22
	1	and @ay<=2001) and cathode		
29	1	6251283.pn.	USPAT	2003/11/25
			1	14:23
30	1	6251238.pn.	USPAT	2003/11/25
		-		14:23
_	16979	cathode and (etch or etching or	USPAT	2003/11/25
		electro\$1etch\$3 or electro\$1polish\$3)	1	10:34
-	9350	(cathode and (etch or etching or	USPAT	2003/11/04
	1	electro\$letch\$3 or electro\$lpolish\$3))		10:54
		and semiconductor		
-	7335	((cathode and (etch or etching or	USPAT	2003/11/04
	1	electro\$1etch\$3 or electro\$1polish\$3))		10:55
		and semiconductor) and (plate or mask)		0000 (11 1/0)
-	5378	(((cathode and (etch or etching or	USPAT	2003/11/04
		electro\$1etch\$3 or electro\$1polish\$3))		10:57
		and semiconductor) and (plate or mask))		
	2024	and power	TICDAM	2003/11/04
-	3614	((((cathode and (etch or etching or	USPAT	2003/11/04
		electro\$letch\$3 or electro\$lpolish\$3))		10:57
	1	and semiconductor) and (plate or mask)) and power) and anode	1	1
_	1242	(((((cathode and (etch or etching or	USPAT	2003/11/04
	12.42	electro\$1etch\$3 or electro\$1polish\$3))	552711	11:04
	i i	and semiconductor) and (plate or mask))		1
	1	and power) and anode) and (cathode same		
		(etch or etching or electro\$letch))		
_	438	((((((cathode and (etch or etching or	USPAT	2003/11/04
	1	electro\$letch\$3 or electro\$lpolish\$3))		11:18
		and semiconductor) and (plate or mask))		
	1	and power) and anode) and (cathode same		
		(etch or etching or electro\$1etch))) not		
	1	plasma		
-	432	((((((cathode and (etch or etching or	USPAT	2003/11/04
		electro\$1etch\$3 or electro\$1polish\$3))		11:19
		and semiconductor) and (plate or mask))		
		and power) and anode) and (cathode same		
		(etch or etching or electro\$1etch))) not		
	1	plasma) and @ay<=2001	******	0003/11/04
-	266	(((((((cathode and (etch or etching or	USPAT	2003/11/04
		electro\$letch\$3 or electro\$1polish\$3))	1	11:19
		and semiconductor) and (plate or mask))		
		and power) and anode) and (cathode same (etch or etching or electro\$1etch))) not		
		plasma) and Gay<=2001) and (solution or		
	1	etchant or wet)		
-	198	((((((((cathode and (etch or etching or	USPAT	2003/11/04
	150	electro\$1etch\$3 or electro\$1polish\$3))		11:31
	1	and semiconductor) and (plate or mask))	ł	
		and power) and anode) and (cathode same		
		(etch or etching or electro\$letch))) not		
	1	plasma) and @ay<=2001) and (solution or		
	1	etchant or wet)) and mask	1	

	_			
-	142		USPAT	2003/11/04
	!	electro\$1etch\$3 or electro\$1polish\$3))		11:32
		and semiconductor) and (plate or mask))		
		and power) and anode) and (cathode same		l i
		(etch or etching or electro\$1etch))) not		į į
		plasma) and @ay<=2001) and (solution or		
		etchant or wet)) and mask) not (emit or		ŀ
		emiting)		
-	47	("1166378"   "1393315"   "2689216"	USPAT	2003/11/04
		"2923671"   "3300396"   "3317410"		11:41
		"3558464"   "3652442"   "3808071"		
		"3809642"   "3953276"   "3962047"		
		"3986911"   "4032422"   "4118303"		
i		"4233416"   "4304641"   "4323438"		
		"4466864"   "4469564"   "4596637"		
		"4664760"   "4906341"   "4931150"		
		"4966647"   "5000827"   "5023044"		
		"5152878"   "5222310"   "5228966"		
		"5284554"   "5308447"   "5318683"		
		"5377708"   "5391285"   "5421987"		1
		"5429733"   "5431823"   "5435885"		1
}		"5437777"   "5443707"   "5447615"		
		"5486282"   "5543032"   "5807165"		
		"5865984"   "5911619").PN.		
_	53		HCDAM	2002/21/04
	33	electro\$1etch\$3 and semiconductor and	USPAT	2003/11/04
		cathode and anode		11:49